

Product Summary

V _{(BR)DSS}	R _{D(on)MAX}	I _D
-60V	65mΩ@-10V	-16A
	85mΩ@-4.5V	

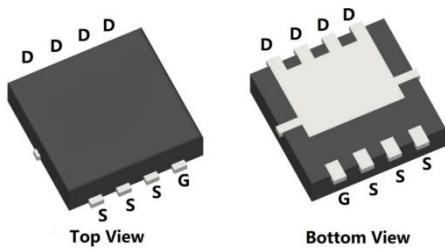
Feature

- High power and current handing capability
- Surface mount package
- Suffix “-Q1” for AEC-Q101

Application

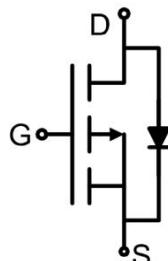
- Power management
- Load switch

Package

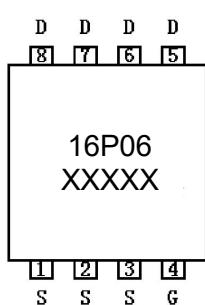


PDFN3.3*3.3-8L

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	-16	A
Pulsed Drain Current	I _{DM}	-64	A
Power Dissipation	P _D	30	W
Thermal Resistance Junction-to-Case ¹⁾	R _{θJA}	4.2	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_c=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2	V
Drain-source on-resistance ³⁾	R _{DS(on)}	V _{GS} =-10V, I _D =-8A		55	65	mΩ
		V _{GS} =-4.5V, I _D =-8A		70	85	
Dynamic characteristics⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, f =1MHz		1153		pF
Output Capacitance	C _{oss}			93.7		
Reverse Transfer Capacitance	C _{rss}			77.7		
Total Gate Charge	Q _g	V _{DS} =-30V, V _{GS} =-10V I _D =-8A		15.8		nC
Gate-Source Charge	Q _{gs}			2.7		
Gate-Drain Charge	Q _{gd}			3.5		
Turn-on delay time	t _{d(on)}	V _{DS} =-30V, V _{GS} =-10V R _L =6Ω, R _G =3Ω		8		nS
Turn-on rise time	t _r			5		
Turn-off delay time	t _{d(off)}			32		
Turn-off fall time	t _f			8		
Source-Drain Diode characteristics						
Diode Forward Current ²⁾	I _S				-16	A
Diode Forward voltage ³⁾	V _{SD}	V _{GS} =0V, I _S =-8A			-1.2	V
Reverse Recovery Time	T _{rr}	I _F =-8A, di/dt =-100A/μs ³⁾ T _J =25°C		27		nS
Reverse Recovery Charge	Q _{rr}			32		nC

Notes:

1) Repetitive Rating: Pulse width limited by maximum junction temperature.

2) Surface Mounted on FR4 Board, t ≤ 10 sec.

3) Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%.

4) Guaranteed by design, not subject to production testing.

Typical Characteristics

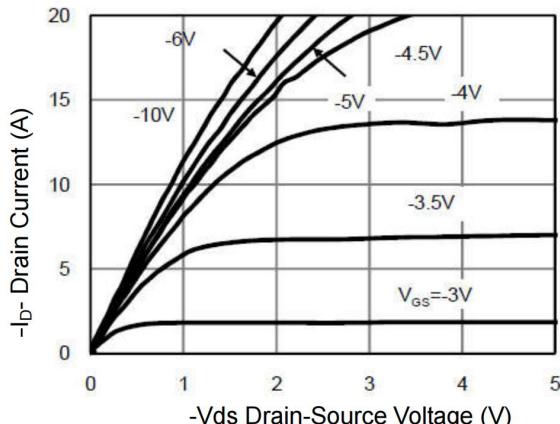


Figure 1 Output Characteristics

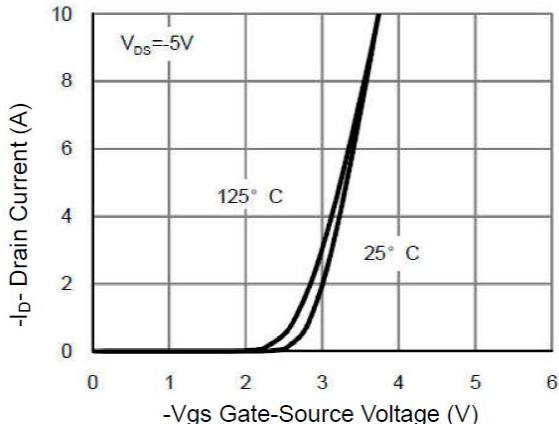


Figure 2 Transfer Characteristics

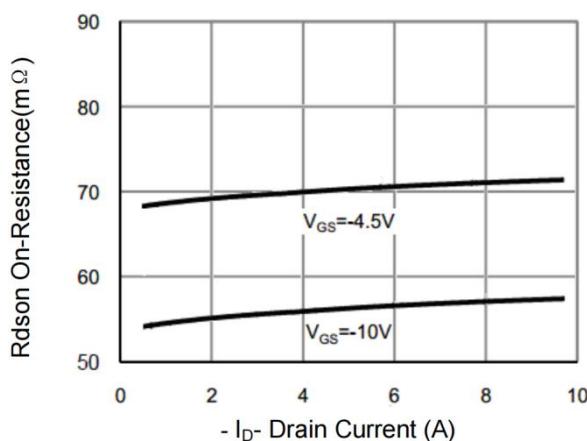


Figure 3 Rdson- Drain Current

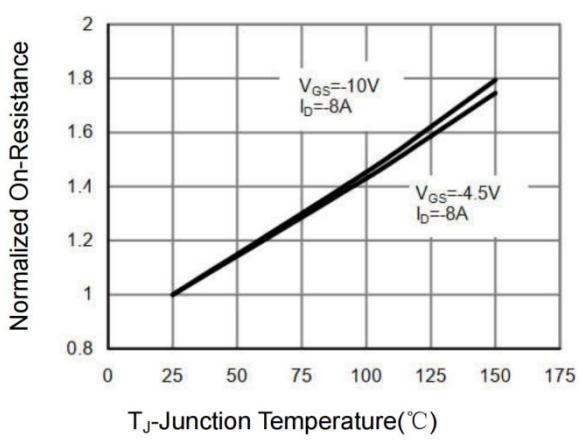


Figure 4 Rdson-Junction Temperature

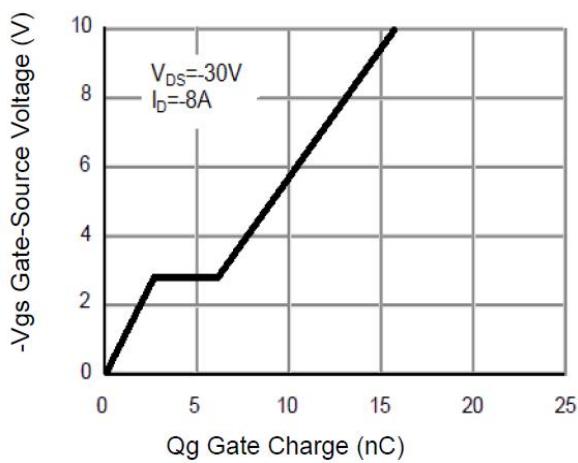


Figure 5 Gate Charge

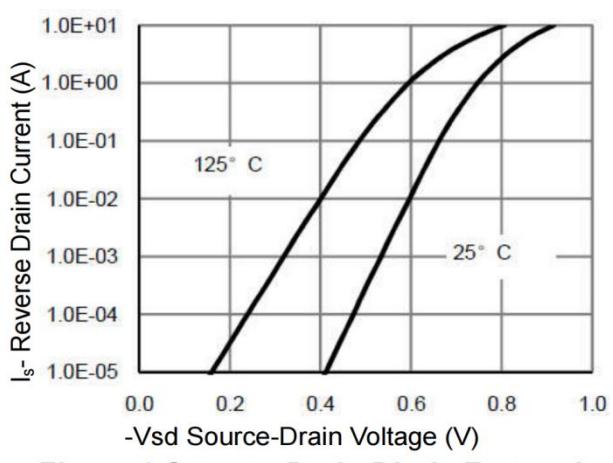


Figure 6 Source- Drain Diode Forward

Typical Characteristics

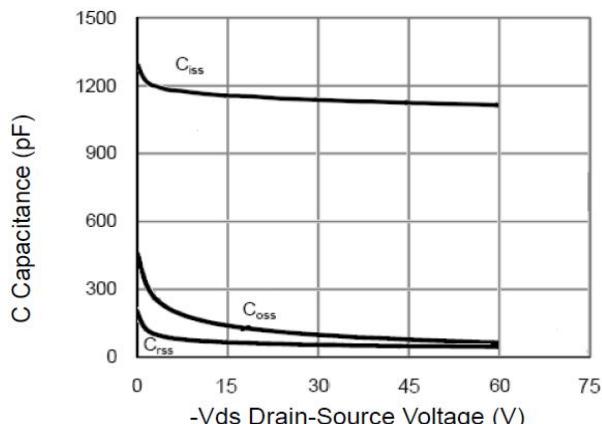


Figure 7 Capacitance vs V_{ds}

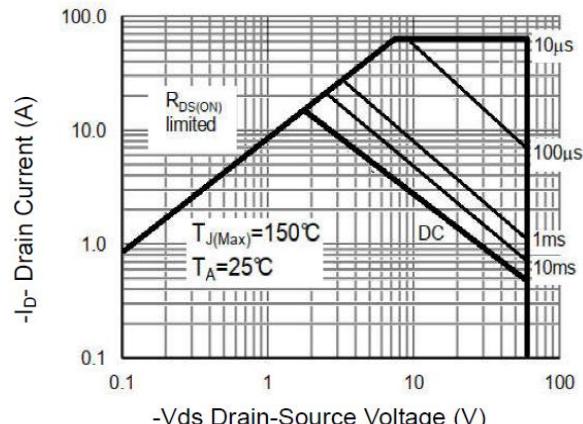


Figure 8 Safe Operation Area

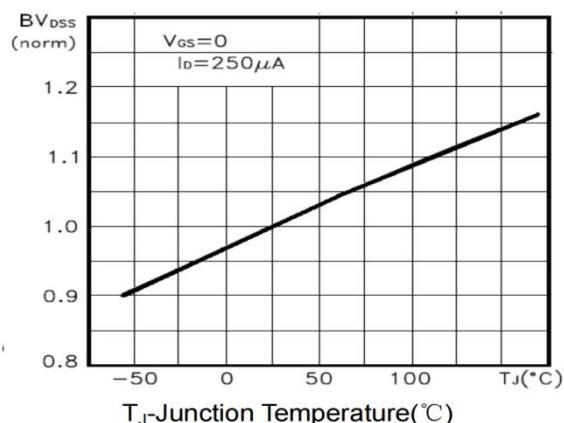


Figure 9 BV_{DSS} vs Junction Temperature

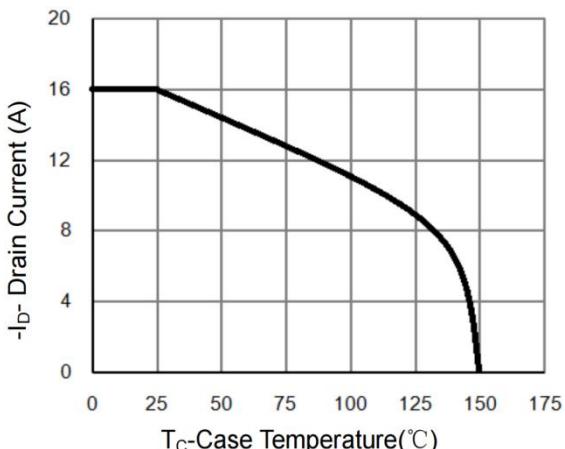


Figure 10 ID Current De-rating

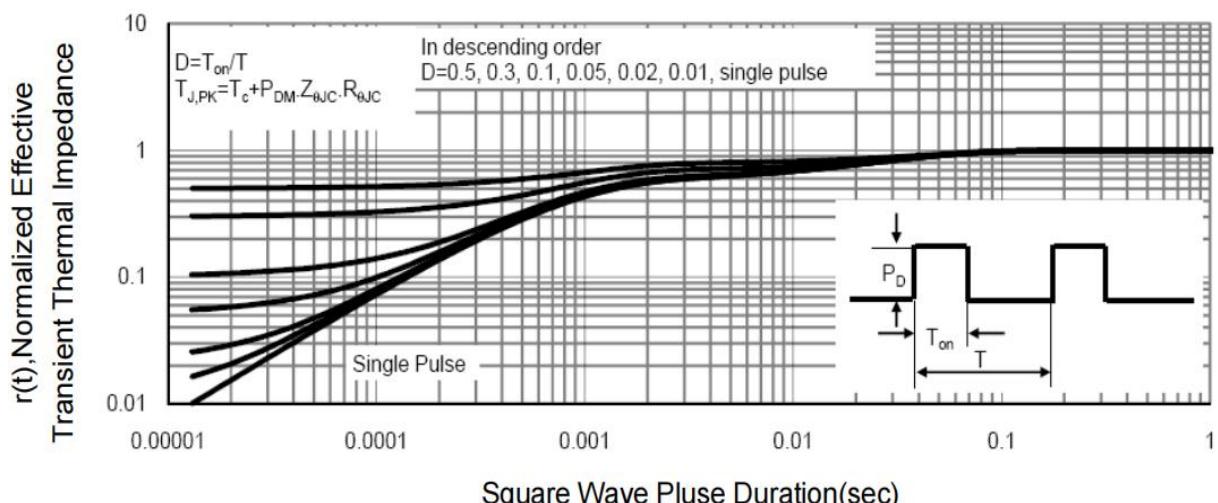
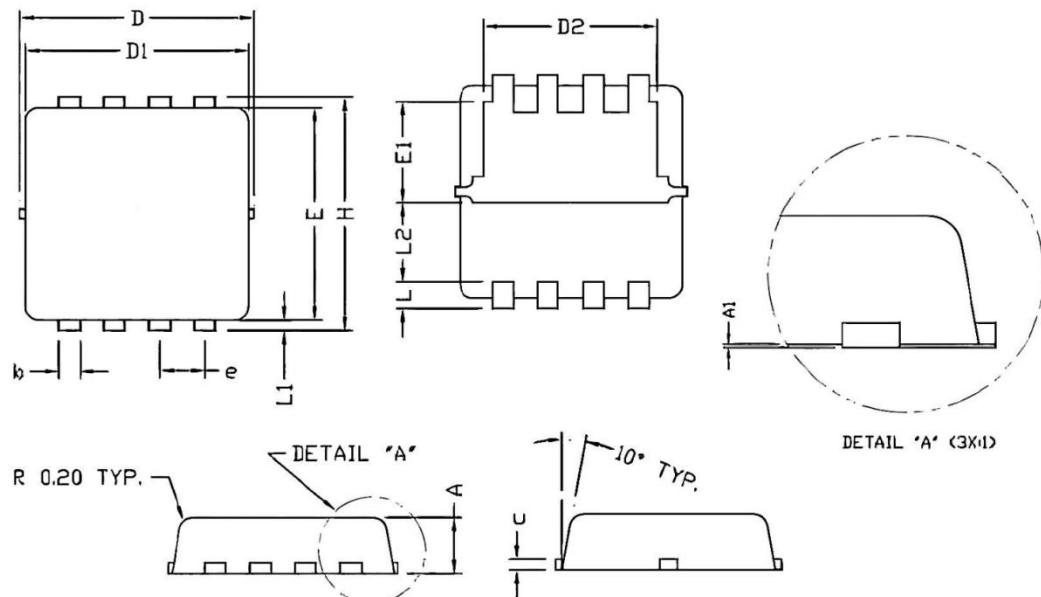


Figure 11 Normalized Maximum Transient Thermal Impedance

PDFN3.3*3.3-8L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.050	0.000	0.002
b	0.240	0.350	0.009	0.014
c	0.100	0.200	0.004	0.008
D	3.250	3.400	0.128	0.134
D1	3.050	3.250	0.120	0.128
D2	2.400	2.600	0.094	0.102
E	3.000	3.200	0.118	0.126
E1	1.350	1.550	0.053	0.061
e	0.650 BSC.		0.026 BSC.	
H	3.200	3.400	0.126	0.134
L	0.300	0.500	0.012	0.020
L1	0.100	0.200	0.004	0.008
L2	1.130 REF.		0.044 REF.	